High Power / High Speed MQW IR-Chip

131254-940

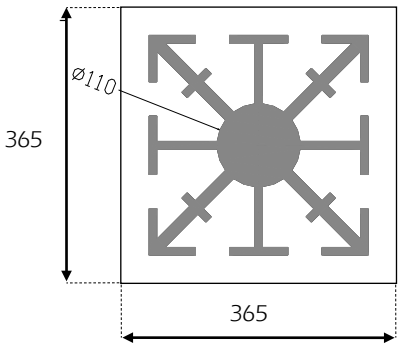
• Mechanical Specification:

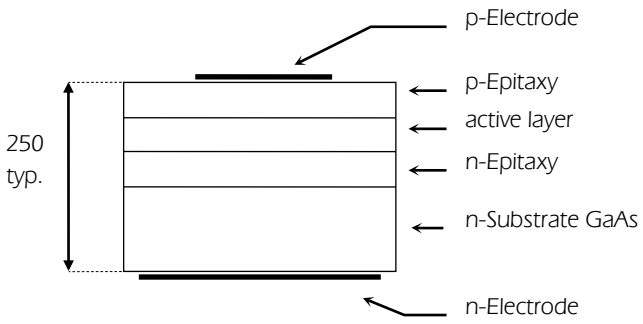
Dimension

- Chip size: 365 x 365µm
- Thickness: typ. 250µm
- P Bonding Pad: 110µm

Electrodes / Metallization

- p-side (anode): Au alloy
- n-side (cathode) Au alloy





• Electrical and Optical Characteristics (T=25°C):

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If = 20mA		1.20	1.40	V
Reverse Current	Ir	Vr = 5V			10	µA
Output Power [1]	Φe	If = 20mA	1.6	2.0		mW
Switching Time	tr, tf	If = 20mA		20		ns
FWHM	½ λp	If = 20mA		20		nm
Peak Wavelength	λp	If = 20mA		940		nm

NOTE:

(1) Power is measured by OSA on gold plate

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• Packing / Labeling:

Dice on adhesive film: 1) wire bond side on top (Standard)
2) back contact on top



• General Remarks:

"RoHS-compliant", fulfill the requirements of RoHS Directive 2002/95/EC
"REACH- compliant"

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use OSA Opto Light products for any unintended or unauthorized application, the buyer shall indemnify OSA Opto Light against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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